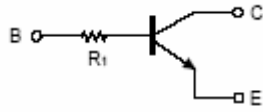


**PNP Transistors**

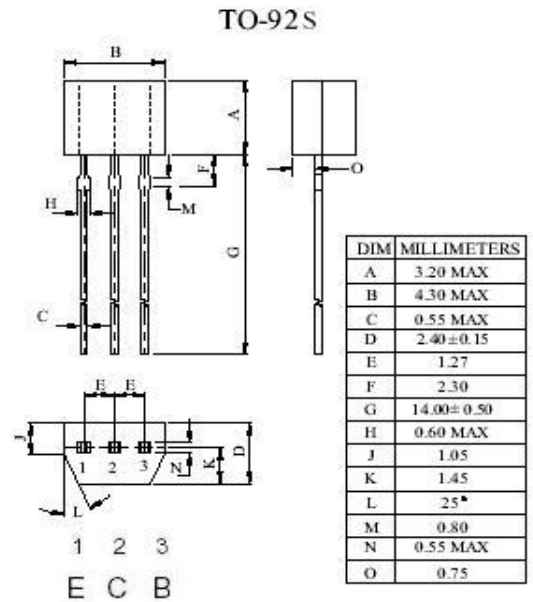
—NPN Silicon—

■■ **APPLICATION:** Interface Circuit and Driver Circuit Applications.



■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Breakdown Voltage	$V_{CBO}$	50	V
Collector-Emitter Breakdown Voltage	$V_{CEO}$	50	V
Emitter-Base Breakdown Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	0.1	A
Power Dissipation	$P_C$	0.3	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	$BV_{CBO}$	50			V	$I_C=50\mu A$ $I_E=0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	50			V	$I_C=1mA$ $I_B=0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	5			V	$I_E=50\mu A$ $I_C=0$
Collector Cut-off Current	$I_{CBO}$			0.5	$\mu A$	$V_{CB}=50V$ $I_E=0$
Emitter Cut-off Current	$I_{EBO}$			0.5	$\mu A$	$V_{EB}=4V$ $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_C=5mA$ $I_B=0.25mA$
DC Current Gain	$h_{FE}$	100	250	600	$\beta$	$V_{CE}=5V$ $I_C=1mA$
Input Resistance	$R_1$	3.29	4.7	6.11	$K\Omega$	
Gain bandwidth product	$f_T$		250		MHZ	$V_{CE}=10V$ $I_E=-5mA$ $f=100MHZ$

■■  $h_{FE}$  Classification And Marking

Mark	C143TS
Classification	
$h_{FE}$	100-600